TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

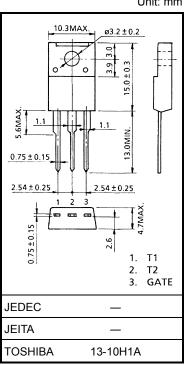
SM2GZ47, SM2GZ47A, SM2JZ47, SM2JZ47A

AC POWER CONTROL APPLICATIONS

- IT (RMS) = 1A (Ta = 65°C without radiator)
- Gate Trigger Current: IGT = 5mA Max. (TYPE "A") •
- Repetitive Peak Off-State Voltage: VDRM = 400V, 600V
- R.M.S On-State Current: IT (RMS) = 2A (Tc = 110°C)
- Isolation Voltage: VISOL = 1500V (AC, t = 60s)

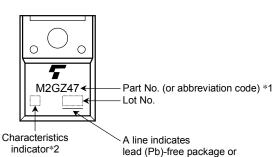
MAXIMUM RATINGS

| CHARACTER | ISTIC | SYMBOL | RATING | UNIT | |
|---|---------------------|---------------------|------------|------|--|
| Repetitive Peak Off-State Voltage and | SM2GZ47 SM2GZ47A | V _{DRM} | 400 | V | |
| Repetitive Peak Reverse Voltage | SM2JZ47 SM2JZ47A | * DRIVI | 600 | | |
| R.M.S On-State Current (Full Sine Waveform) | Tc = 110°C | | 2 | A | |
| | Ta = 65°C | IT (RMS) | 1 | | |
| Peak One Cycle Surge On-State Current (Non-Repetitive) | | | 8 (50Hz) | А | |
| | | ITSM | 8.8 (60Hz) | A | |
| I2t Limit Value | | I2t | 0.32 | A2s | |
| Peak Gate Power Dissipation | | P _{GM} | 3 | W | |
| Average Gate Power D | issipation | P _{G (AV)} | 0.3 | W | |
| Peak Gate Voltage | | V _{FGM} | 10 | V | |
| Peak Gate Current | | I _{GM} | 1.6 | А | |
| Junction Temperature | | Tj | -40~125 | °C | |
| Storage Temperature Range | | T _{stg} | -40~125 | °C | |
| Isolation Voltage (AC, t | = 1min.) | V _{ISOL} | 1500 | V | |



Weight: 1.7 g (typ.)

MARKING



lead (Pb)-free finish.

| | Part No. (or abbreviation code) | Part No. | | |
|----|------------------------------------|--------------------|--|--|
| *1 | M2GZ47 | SM2GZ47, SM2GZ47A | | |
| | M2JZ47 | SM2JZ47, SM2JZ47A | | |
| *2 | Nothing | SM2GZ47, SM2JZ47 | | |
| | A | SM2GZ47A, SM2JZ47A | | |

Unit: mm

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | | MIN | TYP. | MAX | UNIT | |
|-----------------------------------|----------------------|-----------------------|------------------------------------|--|-------------------|------|-----|------|----|
| Repetitive Peak Off-State Current | | I _{DRM} | V _{DRM} = Rated | | _ | — | 20 | μA | |
| Gate Trigger Voltage | | - V _{GT} | V _D = 12V | T2 (+) , Gate (+) | | _ | 1.5 | v | |
| | | | | T2 (+) , Gate (-) | | — | 1 | | |
| | | III | VGT | R _L = 20Ω | T2 (-) , Gate (-) | _ | - | 1 | V |
| | | IV | | | T2 (-) , Gate (+) | - | _ | — | |
| Gate Trigger Current | | Ι | IGT | V _D = 12V R _L = 20Ω | T2 (+) , Gate (+) | _ | - | 8 | mA |
| | SM2GZ47 SM2JZ47 | П | | | T2 (+) , Gate (-) | - | _ | 8 | |
| | | Ш | | | T2 (-) , Gate (-) | _ | _ | 8 | |
| | | IV | | | T2 (-) , Gate (+) | - | _ | — | |
| | SM2GZ47A SM2JZ47A | I | | | T2 (+) , Gate (+) | - | _ | 5 | |
| | | П | | | T2 (+) , Gate (-) | _ | _ | 5 | |
| | | Ш | | | T2 (-) , Gate (-) | - | _ | 5 | |
| | | IV | | | T2 (-) , Gate (+) | - | _ | _ | |
| Peak On-State Voltage | | V _{TM} | I _{TM} = 3A | | - | _ | 1.7 | V | |
| Gate Non-Trigger Voltage | | V _{GD} | V _D = Rated, Tc = 125°C | | 0.2 | _ | _ | V | |
| Holding Current | | Ι _Η | R _L = 100Ω | | - | _ | 10 | mA | |
| Thermal Resistance | | R _{th (j−a)} | Junction to Ambient, AC | | _ | _ | 55 | °C/W | |

2.0

1.5

1.0

0.5

0

-40

0

40

CASE TEMPERATURE Tc (°C)

80

120

25℃

VGŢ

ċ

40°C IGT

GI

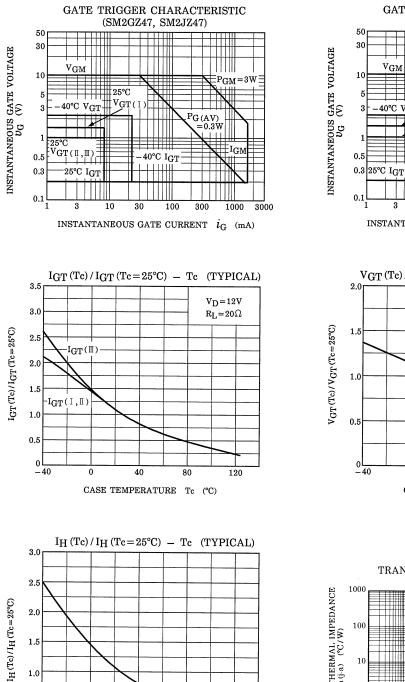
VGM

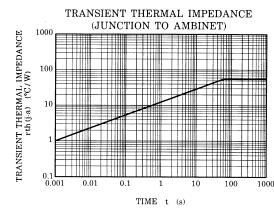
40°C VGT

GATE TRIGGER CHARACTERISTIC (SM2GZ47A, SM2JZ47A)

PG (AV)

PGM=3W=





40

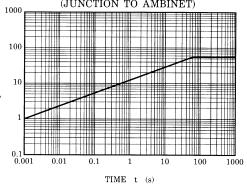
CASE TEMPERATURE Tc (°C)

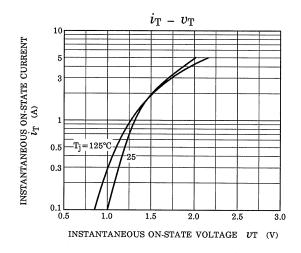
80

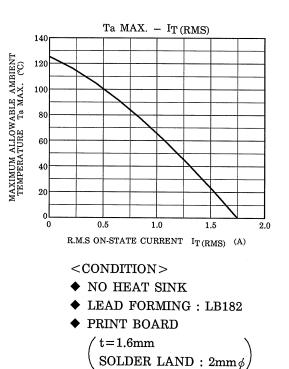
120

0

10 30 100 300 1000 3000 3 INSTANTANEOUS ON-STATE VOLTAGE $i_{
m G}$ (mA) V_{GT} (Tc) / V_{GT} (Tc = 25°C) – Tc (TYPICAL) $V_D = 12V$ $R_L = 20\Omega$







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